Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp	
L1	3	(non adj volatile) and falsh	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 14:30	
L3	483783	(electrically adj3 memory) or (erasable adj3 memory) or (\$1eprom) or (flash or non-volatile or (non adj volatile) adj3 (memory or cell)) or ((non adj volatile) or nonvolatile or non-volatile) adj3 (memory or cell) or nvm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:04	
L4	1206	365/185.21	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:06	
L5	24	4 and (voltage adj regulation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:06	
L6	467	4 and ((non adj volatile) and flash)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:07	
L7	158	6 and ((memory adj cell adj matrix) or (column adj decoder))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:06	
L8	7	7 and (voltage adj regulation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:06	
L9	2314	365/185.18	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:07	
L10	57	9 and (voltage adj regulation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:07	

L11	26	10 and ((non adj volatile) and flash)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:07	
L12	777	365/185.19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:07	
L13	11	12 and (voltage adj regulation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:07	
L14	1156	365/185.09	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:07	
L15	455	14 and ((non adj volatile) and flash)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	JSPAT; EPO; JPO; DERWENT;		2005/12/01 15:07	
L16	4	15 and (voltage adj regulation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:07	
S1	480876	(electrically adj3 memory) or (erasable adj3 memory) or (\$1eprom) or (flash or non-volatile or (non adj volatile) adj3 (memory or cell)) or ((non adj volatile) or nonvolatile or non-volatile) adj3 (memory or cell) or nvm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 13:45	
S2	10582	voltage adj regulation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:06	
S3	1243	S1 and S2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 13:44	
S4	14	S3 and (memory adj cell adj matrix)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2005/11/18 13:57	

S5	69	S3 and (column adj decoder)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 13:56
S6	78	S3 and ((memory adj cell adj matrix) or (column adj decoder))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:06
S7	36	(program\$3 adj load adj circuit) and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:24
S8	3	(non adj volatile) and falsh	US-PGPUB;	OR	ON	2005/11/30 16:30
	*		USPAT; EPO; JPO;			
			DERWENT;	. (
S9	46361	(non adi volatile) and flach	IBM_TDB US-PGPUB;	OB	ON	2005/12/01 15:05
39	40301	(non adj volatile) and flash	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:05
S10	12273	S9 and eras\$3	US-PGPUB;	OR	ON	2005/11/18 16:24
			USPAT; EPO; JPO;	the second		
	K. N.		DERWENT;			
S11	11157	C10 and road#2	IBM_TDB	OR	ON	2005/11/10 16:25
511	1115/	S10 and read\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2005/11/18 16:25
S12	8649	S11 and writ\$5	US-PGPUB;	OR	ON	2005/11/18 16:25
			USPAT; EPO; JPO;			
€	* * * *		DERWENT; IBM_TDB	*	· · · · · · · · · · · · · · · · · · ·	
S13	178	S12 and (program\$3 adj load)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:25
S14	110	S13 and ground	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:31

S15	69	S14 and active	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:27
S16	3	"6603681"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 16:30

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GAU: 2824 Classification: 365/185.210

10/789351
Inventor: MARTINES, IGNAZIO, et al
Status: 30 - DOCKETED NEW CASE - READY FOR EXAMINATION
Title: VOLTAGE REGULATION SYSTEM FOR A MULTIWORD PROGRAMMING OF A LOW INTEGRATION AREA NON VOLATILE MEMORY

All tab report (16 items, not sorted)

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Fee Worksheet (PTO-875)	Oath or Declaration filed	Drawings	Abstract	Claims	Specification	Transmittal letter	Pre-Exam Formalities Notice	Foreign Priority Papers Filed	NPL Documents	Information Disclosure Statement (IDS) Filed	Foreign Priority Papers Filed	Oath or Declaration filed	Applicant Response to Pre-Exam Formalities Notice	DocumentType
02/26/2004	02/26/2004	02/26/2004	02/26/2004	02/26/2004	02/26/2004	02/26/2004	05/19/2004	07/19/2004	07/19/2004	07/19/2004	07/19/2004	07/19/2004	07 <i>I</i> 19/2004	Date
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										considered 12/1/05				Annotations

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1	Pages
	Annotations
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